Fig. 1. Scheme of the QW structures grown at 450 °C. The shutters time sequence in one cicle of the MME process was:

- Al-2s followed by In-1s for QW1,
- Al-2s followed by In-2s for QW2, and
- Al-1s followed by In-2s for QW3.

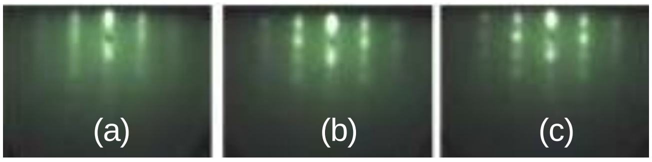

Fig.2. RHEED patterns taken at different stages of the MME process: (a) after the growth of QW1, (b) after growth of QW2, and (c) after growth of QW3.

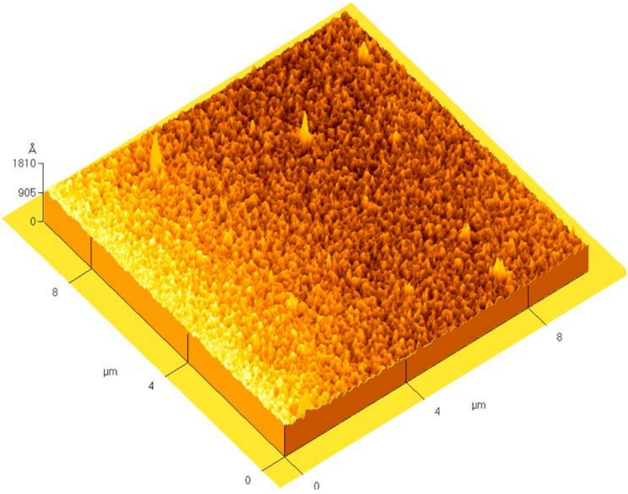

Fig. 3. AFM surface scan over a 10 μm^2 area. The RMS in this region is 8 nm

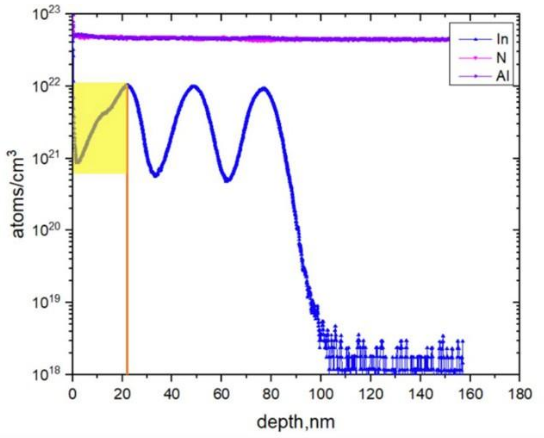

Fig. 4. SIMS depth profiles for In (blue line), Al (purple line), and N (magenta line). The yellow-colored area highlights a region of In segregation.

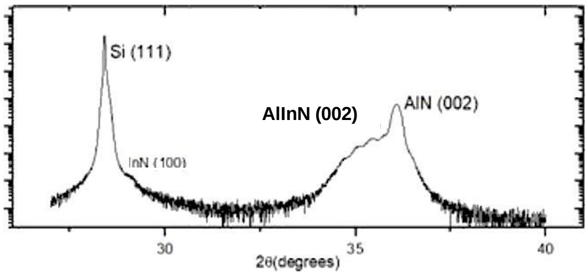

Fig. 5. XRD diffraction plot in the θ-2θ geometry.

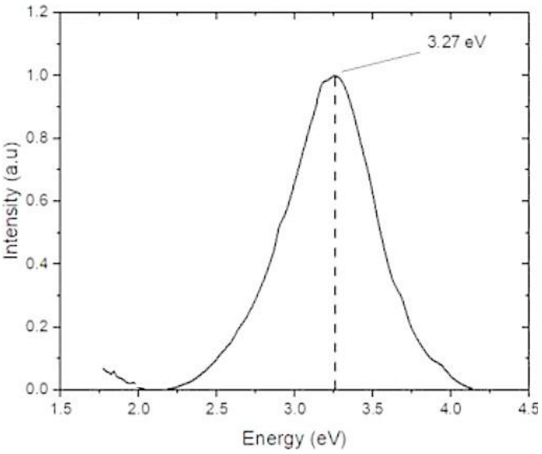

Fig. 6 CL spectrum measured at 300 K.